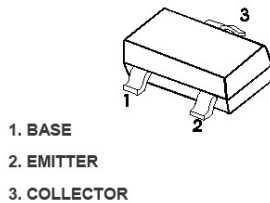




FMMT591

TRANSISTOR (PNP)

SOT-23



Marking: 591

特征 Features

- Low equivalent on-resistance

机械数据 Mechanical Data

- SOT-23 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter -Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	I _C	-1.0	A
Peak Pulse Current	I _{CM}	2.0	A
Collector Power Dissipation	P _C	250	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	500	°C/W

电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits			单位 Unit
			Min	Typ	Max	
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-80			V
Collector-emitter breakdown voltage	V(BR)CEO*	IC=-10mA, IB=0	-60			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100uA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-60V, IE=0			-100	nA
Emitter cut-off current	IEBO	VEB=-4V, IC=0			-100	nA
DC current gain	hFE(1)	VCE=-5V, IC=-1mA	100			
	hFE(2)*	VCE=-5V, IC=500mA	100		300	
	hFE(3)*	VCE=-5V, IC=-1A	80			
	hFE(4)*	VCE=-5V, IC=-2A	15			
Collector-emitter saturation voltage	VCE(sat)*	IC=-500mA, IB=-50mA			-0.30	V
		IC=-1000mA, IB=-100mA			-0.60	V
Base -emitter saturation voltage	VBE(sat)*	IC=-1000mA, IB=-100mA			-1.20	V
Base -emitter voltage	VBE*	VCE=-5V, IC=-1A			-1.00	V
Transition frequency	f _T	VCE=-10V, IC=-50mA, f=100MHz	150			MHz
Collector output capacitance	Cob	VCB=-10V, IE=0, f=1MHz			10	pF

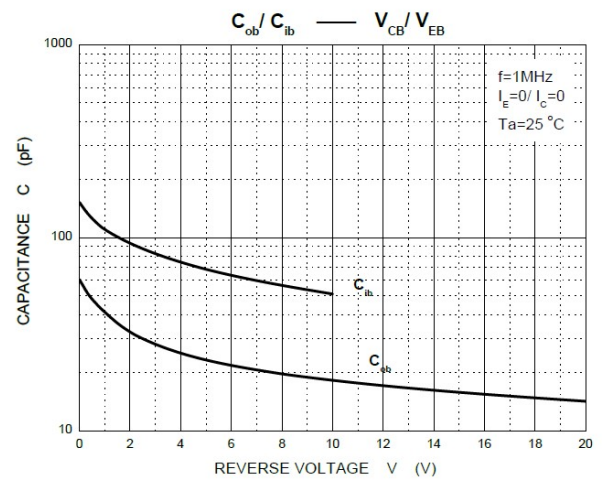
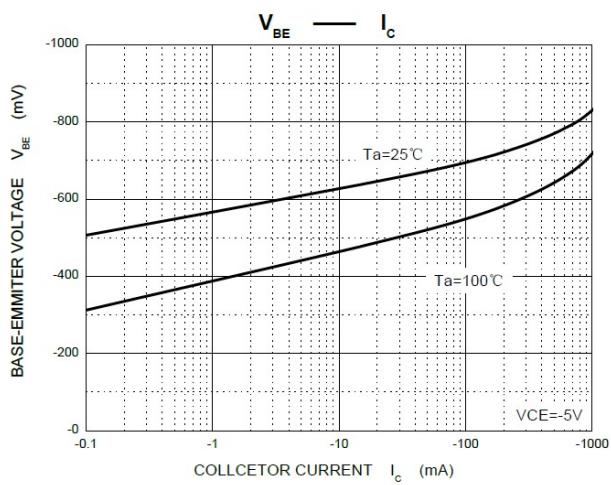
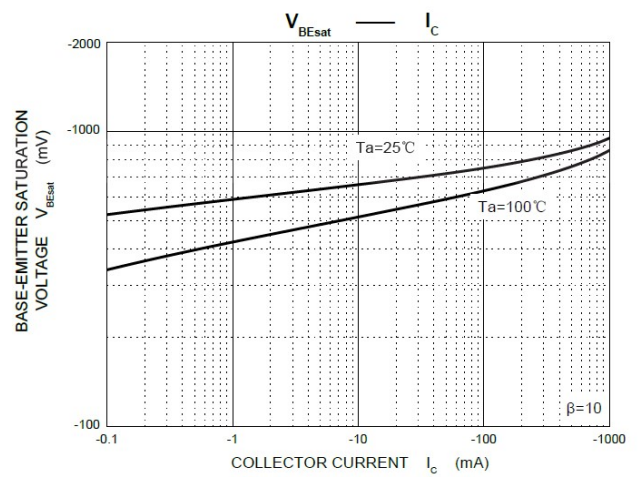
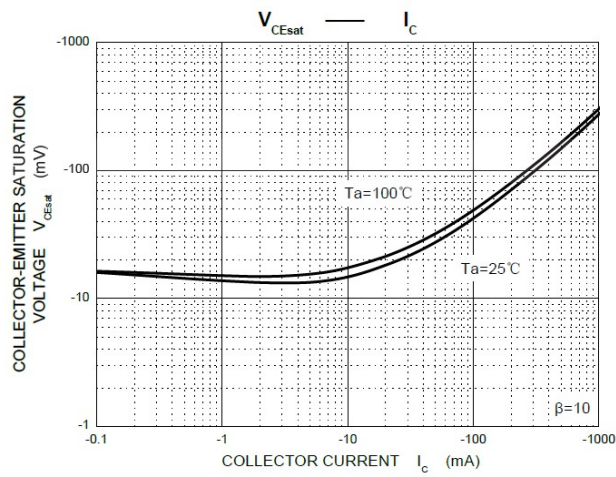
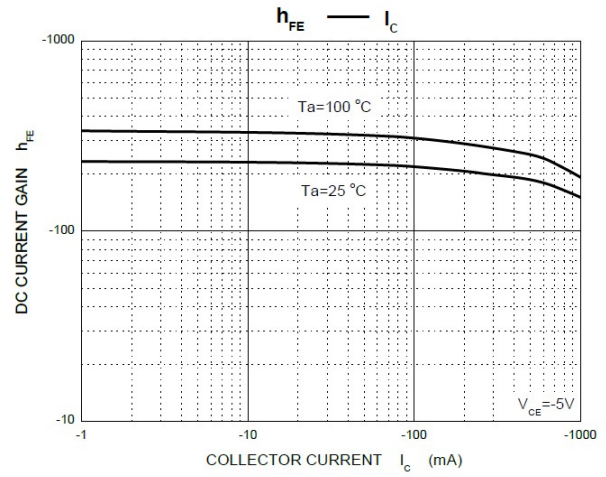
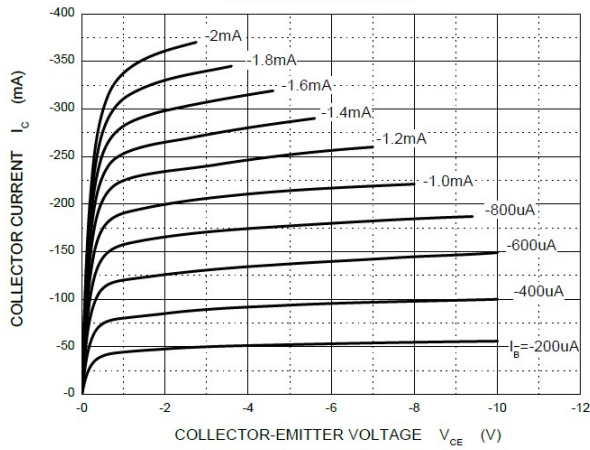
* Measured under pulsed conditions, Pulse width=300us, Duty cycle≤2%



FMMT591

TRANSISTOR (PNP)

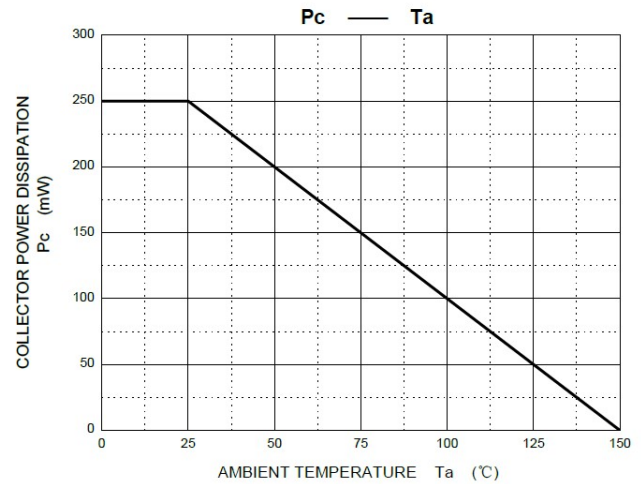
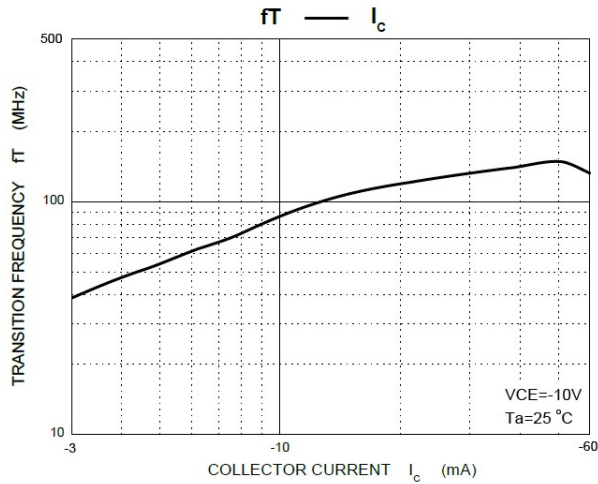
Static Characteristic



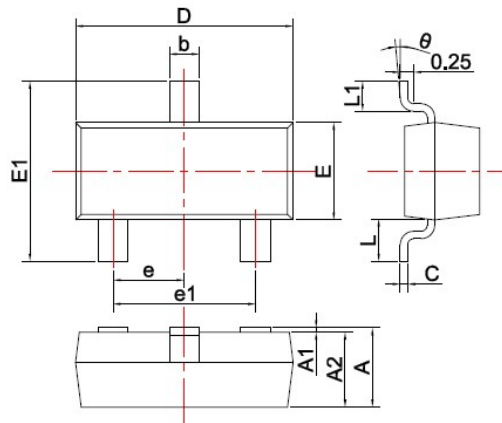


FMMT591

TRANSISTOR (PNP)



SOT-23 PACKAGE OUTLINE Plastic surface mounted package

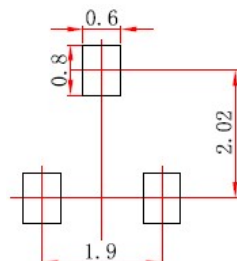


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Unit: mm

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note:

1. Controlling dimension: In millimeters.
2. General tolerance: $\pm 0.05mm$.
3. The pad layout is for reference purposes only.